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 Meets or Exceeds the Requirements of TIA/EIA-232-F and ITU Recommendation V.28 	DW OR N PACKAGE (TOP VIEW)		
 Single Chip With Easy Interface Between UART and Serial-Port Connector 	V _{DD} [1 20] V _{CC} RA1 [2 19] RY1		
 Less Than 9-mW Power Consumption Wide Driver Supply Voltage 4.5 V to 13.2 V 	RA2 [] 3 18] RY2 RA3 [] 4 17] RY3 DY1 [] 5 16] DA1		
 Driver Output Slew Rate Limited to 30 V/µs Max 	DY2 [] 6 15]] DA2 RA4 [] 7 14]] RY4 DY3 [] 8 13]] DA3		
 Receiver Input Hysteresis 1100 mV Typ Push-Pull Receiver Outputs 	RA5 [9 12] RY5 V _{SS} [10 11] GND		
 On-Chip Receiver 1-μs Noise Filter 			

- Functionally Interchangeable With Texas Instruments SN75185
- Operates Up to 120 kbit/s Over a 3-Meter Cable (See Application Information for Conditions)

description

The SN75C185 is a low-power BiMOS device containing three independent drivers and five receivers that are used to interface data terminal equipment (DTE) with data circuit-terminating equipment (DCE). Typically, the SN75C185 replaces one SN75188 and two SN75189 devices. This device conforms to TIA/EIA-232-F. The drivers and receivers of the SN75C185 are similar to those of the SN75C188 and SN75C189A, respectively. The drivers have a controlled output slew rate that is limited to a maximum of 30 V/ μ s, and the receivers have filters that reject input noise pulses that are shorter than 1 μ s. Both these features eliminate the need for external components.

The SN75C185 uses the low-power BiMOS technology. In most applications, the receivers contained in this device interface to single inputs of peripheral devices such as ACEs, UARTS, or microprocessors. By using sampling, such peripheral devices usually are insensitive to the transition times of the input signals. If this is not the case, or for other uses, it is recommended that the SN75C185 receiver outputs be buffered by single Schmitt input gates or single gates of the HCMOS, ALS, or 74F logic families.

The SN75C185 is characterized for operation from 0°C to 70°C.



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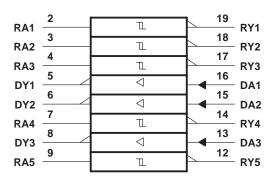
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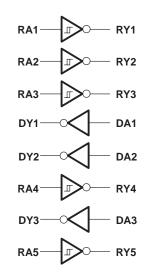
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logic symbol[†]



[†] This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)





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Output

DΫ́

GND

Vss

Output RY

EQUIVALENT DRIVER INPUT EQUIVALENT DRIVER OUTPUT VDD VDD Input Internal DA 1.4-V Ref to GND **160** Ω \mathcal{N} **74** Ω GND VSS **72** Ω EQUIVALENT RECEIVER INPUT EQUIVALENT RECEIVER OUTPUT Vcc Input ŔΑ **3.4 k**Ω ESD Protection **1.5 k**Ω ESD Protection ≶ **530 k**Ω ►

equivalent schematics of inputs and outputs

All resistor values are nominal.



GND

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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)[†]

$\begin{array}{c} -13.5 \ V \\7 \ V \\7 \ V_{SS} \text{ to } V_{DD} \\7 \ V_{SS} \text{ to } V_{DD} \\7 \ V_{SS} \text{ to } V_{DD} \\7 \ V_{SS} - 6 \ V \text{ to } V_{DD} + 6 \ V \\7 \ V_{SS} - 6 \ V \text{ to } V_{CC} + 0.3 \ V \\7 \ S8^{\circ} C/W \\69^{\circ} C/W \end{array}$

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. All voltages are with respect to network GND.

2. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions

			MIN	NOM	MAX	UNIT
		V _{DD}	4.5	12	13.2	V
	Supply voltage	VSS	-4.5	-12	-13.2	V
		VCC	4.5	5	6	V
VI	Input voltage (see Note 3)	Drivers	V _{SS} +2		V _{DD}	v
		Receivers	-25		25	
VIH	High-level input voltage	Drivers	2			V
VIL	Low-level input voltage	Drivers			0.8	V
ЮН	High-level output current	Dessiver			-1	mA
IOL	High-level output current	Receivers			3.2	mA
т _А	Operating free-air temperature	•	0		70	°C

NOTE 3: The algebraic convention, where the more positive (less negative) limit is designated as maximum, is used in this data sheet for logic levels only, e.g., if -10 V is a maximum, the typical value is a more negative voltage.

supply currents

	PARAMETER	TEST CONDITIONS			MIN	TYP	MAX	UNIT
inn	Supply current from Voo	V _{DD} = 5 V,	$V_{SS} = -5 V$		115	200	μA	
^I DD	Supply current norm vDD	All inputs at 2 V or 0.8 V	V _{DD} = 12 V,	$V_{SS} = -12 V$		115	200	μΑ
	Supply current from VSS	No load, All inputs at 2 V or 0.8 V	V _{DD} = 5 V,	$V_{SS} = -5 V$		-115	-200	μA
ISS	Supply current norm VSS		V _{DD} = 12 V,	$V_{SS} = -12 V$		-115	-200	μΑ
	Supply current from Vee	No load	V _{DD} = 5 V,	$V_{SS} = -5 V$			750	μA
CC	ICC Supply current from VCC	V _{DD} = 12 V,	$V_{SS} = -12 V$			750	μΑ	



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DRIVER SECTION

electrical characteristics over operating free-air temperature range, V_{DD} = 12 V, V_{SS} = –12 V, V_{CC} = 5 V $\pm 10\%$ (unless otherwise noted)

	PARAMETER		TEST CONDITIONS			MIN	TYP†	MAX	UNIT
Vall	High-level output voltage	VIL = 0.8 V,	RL = 3 kΩ,	V _{DD} = 5 V,	$V_{SS} = -5 V$	4	4.5		V
VOH	High-level output voltage	See Figure 1		V _{DD} = 12 V	$V_{SS} = -12 V$	10	10.8		v
Vei	Low-level output voltage	VIH = 0.8 V,	$R_L = 3 k\Omega$,	V _{DD} = 5 V,	$V_{SS} = -5 V$		-4.4	-4	V
VOL	(see Note 3)	See Figure 1		V _{DD} = 12 V	$V_{SS} = -12 V$		-10.7	-10	v
Iн	High-level input current	V _I = 5 V, See Figure 2					1	μΑ	
۱ _{IL}	Low-level input current	V _I = 0, See Figure 2					-1	μΑ	
IOS(H)	High-level short-circuit output current (see Note 4)	$V_I = 0.8 V$, $V_O = 0 \text{ or } V_O = V_{SS}$, See Figure 1			-4.5	-12	-19.5	mA	
IOS(L)	Low-level short-circuit output current (see Note 4)	$V_I = 2 V$, $V_O = 0 \text{ or } V_O = V_{DD}$, See Figure 1			4.5	12	19.5	mA	
r _o	Output resistance	V _{DD} = V _{SS} = See Note 5	$V_{DD} = V_{SS} = V_{CC} = 0,$ $V_O = -2 V \text{ to } 2 V,$ See Note 5			300	400		Ω

[†] All typical values are at $T_A = 25 \,^{\circ}C$.

NOTES: 3. The algebraic convention, where the more positive (less negative) limit is designated as maximum, is used in this data sheet for logic levels only, e.g., if -10 V is a maximum, the typical value is a more negative voltage.

4. Not more than one output should be shorted at one time.

5. Test conditions are those specified by TIA/EIA-232-F.

switching characteristics, V_{DD} = 12 V, V_{SS} = –12 V, V_{CC} = 5 V $\pm 10\%,$ T_A = 25°C (unless otherwise noted) (see Figure 3)

	PARAMETER		TEST CONDITIONS		TYP	MAX	UNIT	
^t PLH	Propagation delay time, low- to high-level output (see Note 6)				1.2	3	μs	
^t PHL	Propagation delay time, high- to low-level output (see Note 6)	$R_L = 3 k\Omega \text{ to } 7 k\Omega$, C	$R_L = 3 k\Omega$ to 7 kΩ, $C_L = 15 pF$	$R_L = 3 k\Omega$ to 7 k Ω ,	$R_L = 3 \text{ k}\Omega \text{ to } 7 \text{ k}\Omega, C_L = 15 \text{ pF}$	2.5	3.5	μs
^t TLH	Transition time, low- to high-level output			0.53	2	3.2	μs	
^t THL	Transition time, high- to low-level output			0.53	2	3.2	μs	
^t TLH	Transition time, low- to high-level output (see Note 7)			$R_{I} = 3 k\Omega$ to 7 kΩ, $C_{I} = 2500 pF$		1		μs
^t THL	Transition time, high- to low-level output (see Note 7)	$\Gamma_{L} = 3 \times 2107 \times 22,$	$O_{L} = 2500 \text{ pr}$		1		μs	
SR	Output slew rate (see Note 7)	$R_L = 3 k\Omega$ to 7 kΩ,	C _L = 15 pF	4	10	30	V/µs	

NOTES: 6. tpHL and tpLH include the additional time due to on-chip slew rate and are measured at the 50% points.

 Measured between 3-V and –3-V points of output waveform TIA/EIA-232-F conditions), and all unused inputs are tied either high or low.



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RECEIVER SECTION

electrical characteristics over operating free-air temperature range, V_{DD} = 12 V, V_{SS} = –12 V, V_{CC} = 5 V $\pm 10\%$ (unless otherwise noted)

	PARAMETER		TEST COND	ITIONS	MIN	TYP†	MAX	UNIT	
VIT+	Positive-going input threshhold voltage	See Figure 5			1.6	2.1	2.55	V	
V _{IT} –	Negative-going input threshhold voltage	See Figure 5			0.65	1	1.25	V	
V _{hys}	Input hysteresis voltage (V _{IT +} - V _{IT} _)				600	1100		mV	
		V _I = 0.75 V,	$I_{OH} = -20 \ \mu A$,	See Figure 5 and Note 8	3.5				
Varia	High-level output voltage	VI = 0.75 V,	$V_{CC} = 4.5 V$		2.8	4.4			
Vон		$I_{OH} = -1 \text{ mA},$	$V_{CC} = 5 V$		3.8	4.9		v	
		See Figure 5	V _{CC} = 5.5 V		4.3	5.4			
VOL	Low-level output voltage	V _I = 3 V,	I _{OL} = 3.2 mA,	See Figure 5		0.17	0.4	V	
	High lovel input ourrest	V _I = 3 V			0.43	0.55	1	mA	
IН	High-level input current	V _I = 25 V			3.6	4.6	8.3	mA	
l		V _I = -3 V			-0.43	-0.55	-1	A	
۱L	Low-level input current	V _I = -25 V			-3.6	-5.0	-8.3	mA	
IOS(H)	Short-circuit output at high level	V _I = 0.75 V,	$V_{O} = 0,$	See Figure 4		-8	-15	mA	
IOS(L)	Short-circuit output at low level	$V_{I} = V_{CC},$	$V_{O} = V_{CC},$	See Figure 4		13	25	mA	

[†] All typical values are at $T_A = 25 \,^{\circ}C$.

NOTE 8: If the inputs are left unconnected, the receiver interprets this as an input low, and the receiver outputs remain in the high state.

switching characteristics, V_{DD} = 12 V, V_{SS} = –12 V, V_{CC} = 5 V $\pm 10\%,$ T_A = 25°C (unless otherwise noted) (see Figure 6)

	PARAMETER		TEST CONDITIONS		TYP	MAX	UNIT		
^t PLH	Propagation delay time, low- to high-level output	R _L = 5 kΩ,	R _L = 5 kΩ,	R _L = 5 kΩ,			3	4	μs
^t PHL	Propagation delay time, high- to low-level output				C _I = 50 pF		3	4	μs
t _{TLH}	Transition time, low- to high-level output				$C_{L} = 30 \text{pr}$		300	450	ns
^t THL	Transition time, high- to low-level output				100	300	ns		
^t w(N)	Duration of longest pulse rejected as noise (see Note 9)	$R_L = 5 k\Omega$,	C _L = 50 pF	1		4	μs		

NOTE 9: The receiver ignores any postive- or negative-going pulse that is less than the minimum value of $t_{W(N)}$ and accepts any positive- or negative-going pulse greater than the maximum of $t_{W(N)}$.



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PARAMETER MEASUREMENT INFORMATION

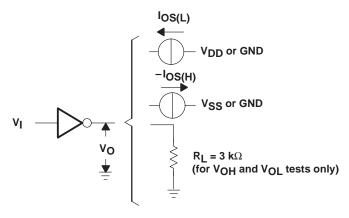


Figure 1. Driver Test Circuit for V_{OH} , V_{OL} , $I_{OS(H)}$, and $I_{OS(L)}$

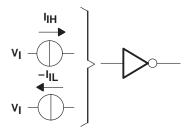


Figure 2. Driver Test Circuit for IIH and IIL

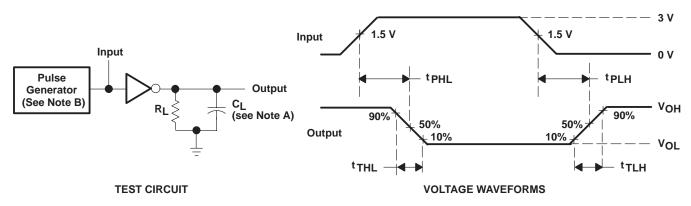




Figure 3. Driver Test Circuit and Voltage Waveforms



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PARAMETER MEASUREMENT INFORMATION

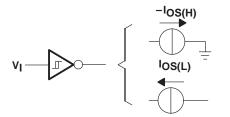


Figure 4. Receiver Test Circuit for IOS(H) and IOS(L)

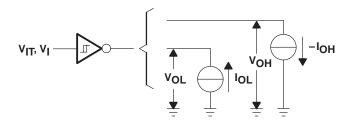
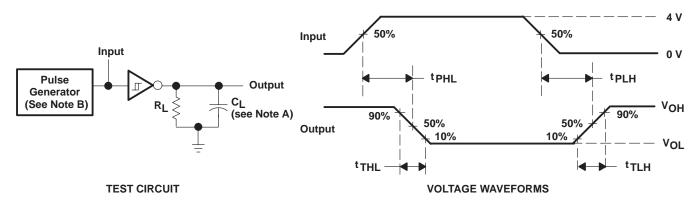
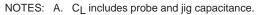


Figure 5. Receiver Test Circuit for VIT, VOH, and VOL



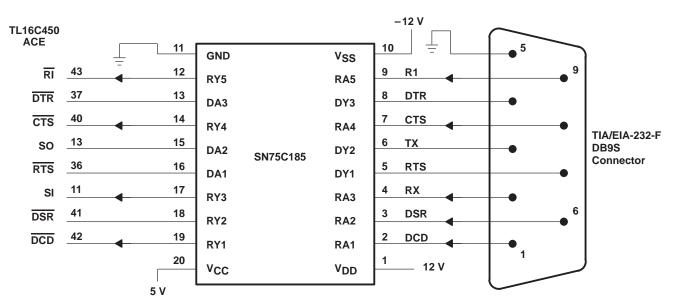


B. The pulse generator has the following characteristics: t_W = 25 µs, PRR = 20 kHz, Z_O = 50 Ω, t_f = t_f < 50 ns.

Figure 6. Receiver Propagation and Transition Times



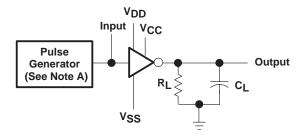
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APPLICATION INFORMATION



The SN75C185 supports data rates up to 120 kbit/s over a 3-meter cable. Laboratory experiments show that, with C_L = 500 pF and R_L = 3 k Ω (minimum RS-232 input resistance load), the device can support this data rate. The 500-pF load approximates a typical 3-meter cable because the maximum RS-232 specification is 2500 pF (or about 15 meters). Figure 8 shows the test circuit used. Temperature was varied from 0°C to 70°C for the experiment.



NOTES: A. The pulse generator has the following characteristics: PRR = 60 kHz (120 kbit/s), $Z_O = 50 \Omega$. B. $V_{CC} = 5 V$, $V_{DD} = 12 V$, $V_{SS} = -12 V$.

Figure 8. Data-Rate Test Circuit



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